



IPP80N06S207AKSA4 Information



For Reference Only

Part Number IPP80N06S207AKSA4
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 55V 80A TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPP80N06S207AKSA4 Specifications

Manufacturer Part Number IPP80N06S207AKSA4 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 180µA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3400pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 6.6 mOhm @ 68A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3		
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 180μA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package PG-TO220-3-1 Package / Case MOSFET (Metal Oxide) 55V 660 MCS 660 (Tc) 80A (Tc) 8	Series	OptiMOS?
Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 180μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 180μA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3400pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 6.6 mOhm @ 68A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 180μAGate Charge (Qg) (Max) @ Vgs110nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3400pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id 4V @ 180μA Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3400pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 6.6 mOhm @ 68A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	80A (Tc)
Gate Charge (Qg) (Max) @ Vgs 110nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3400pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 6.6 mOhm @ 68A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.6 mOhm @ 68A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 180μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	110nC @ 10V
FET Feature - Case - Ca	Input Capacitance (Ciss) (Max) @ Vds	3400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.6 mOhm @ 68A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs6.6 mOhm @ 68A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Power Dissipation (Max)	250W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	6.6 mOhm @ 68A, 10V
Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-3-1
Report errors?	Package / Case	TO-220-3
		Report errors?

IPP80N06S207AKSA4 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP80N06S207AKSA4 Payment Methods



















IPP80N06S207AKSA4 Shipping Methods













If you have any question about IPP80N06S207AKSA4, please do not hesitate to contact us!

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